In the Claims:

1. (currently amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method or slicing the silicon single crystal ingot and cleaning the wafer,

wherein said wafer has a wafer surface formed by said slicing of the silicon single crystal or by said slicing and cleaning, the wafer surface including [[includes]] an area in which crystal originated particles are generated,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 15 counts/cm^2, even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH_4OH, H_2O_2, and H_2O.

2. (original) A silicon single crystal wafer for a particle monitor according to Claim 1, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm^3 (old ASTM).

3. (currently amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein said wafer has a wafer surface formed by said slicing of the silicon single crystal or by said slicing and cleaning, the wafer surface including [[includes]] an area in which crystal originated particles are generated, and further said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}$ atoms/cm^3,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 1 count/cm^2, even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH_4OH, H_2O_2, and H_2O.

4. (original) A silicon single crystal wafer for a particle monitor according to Claim 3, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm^3 (old ASTM).

5. (currently amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein said wafer has a wafer surface formed by said slicing of the silicon single crystal or by said slicing and cleaning, forming of the ingot [[includes,]] in said Czochralski method, including controlling a [[the]] time period of passing [[the]] a temperature range from 1150°C to 1070°C [[is]] to be within 20 min and controlling a [[the]] time period of passing [[the]] a temperature range from 900°C to 800°C [[is]] to be within 40 min,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 15 counts/cm^2, even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH_4OH, H_2O_2, and H_2O.

6. (original) A silicon single crystal wafer for a particle monitor according to Claim 5, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm^3 (old ASTM).

7. (currently amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein in said Czochralski method, a [[the]] time period of passing [[the]] a temperature range from 1150°C to 1070°C is within 20 min and a [[the]] time period of passing [[the]] a temperature range from 900°C to 800°C is within 40 min,

wherein said silicon single crystal ingot has a nitrogen concentration of 1×10^{13} – 1×10^{15} atoms/cm^3,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 1 count/cm^2, even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH_4OH, H_2O_2, and H_2O.

8. (original) A silicon single crystal wafer for a particle monitor according to Claim 7, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm^3 (old ASTM).

9. (previously presented) A silicon single crystal wafer for a particle monitor according to Claim 1, wherein, in said Standard Cleaning - 1, a chemical component of

a used solution is H_2O_2 : NH_4OH : H_2O = 1 : 1 :5, the cleaning is repeated six times, and each cleaning is carried out for 10 min.

10. (previously presented) A silicon single crystal wafer for a particle monitor according to Claim 3, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is H_2O_2 : NH_4OH : H_2O = 1 : 1 :5, the cleaning is repeated six times, and each cleaning is carried out for 10 min.

11. (previously presented) A silicon single crystal wafer for a particle monitor according to Claim 5, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is H_2O_2 : NH_4OH : H_2O = 1 : 1 :5, the cleaning is repeated six times, and each cleaning is carried out for 10 min.

12. (previously presented) A silicon single crystal wafer for a particle monitor according to Claim 7, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is H_2O_2 : NH_4OH : H_2O = 1 : 1 :5, the cleaning is repeated six times, and each cleaning is carried out for 10 min.

13. (new) A silicon single crystal wafer for a particle monitor according to claim 5, wherein <u>said wafer surface is either a sliced wafer surface formed as a result of said slicing of the silicon single crystal or a sliced and cleaned wafer surface formed as a result of said slicing of the silicon single crystal and cleaning thereof.</u>

14. (new) A silicon single crystal wafer for a particle monitor according to claim 7, wherein said wafer surface is either a sliced wafer surface formed as a result of said slicing of the silicon single crystal or a sliced and cleaned wafer surface formed as a result of said slicing of the silicon single crystal and cleaning thereof.